



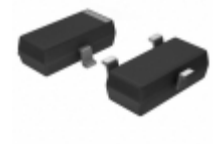
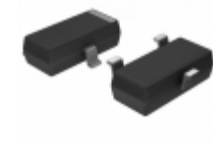
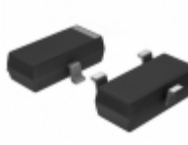


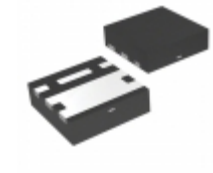
	<b>DMN30H4D0LFDE-7</b>	
	<b>Hersteller-Teilenummer:</b>	DMN30H4D0LFDE-7
	<b>Hersteller / Marke:</b>	Diodes Incorporated
	<b>Teil der Beschreibung:</b>	MOSFET N-CH 300V .55A 6UDFN
<p>Image may be representation. See specs for product details.</p>	<b>Datenblätter:</b>	 <a href="#">DMN30H4D0LFDE-7.pdf</a>
	<b>RoHs Status:</b>	Bleifrei / RoHS-konform
	<b>Lagerzustand:</b>	New original, 3000 pcs Stock Available.
	<b>Liefern von:</b>	Hong Kong
	<b>Versandweg:</b>	DHL/Fedex/TNT/UPS/EMS

### Spezifikationen

Teilenummer	DMN30H4D0LFDE-7
Hersteller	Diodes Incorporated
Beschreibung	MOSFET N-CH 300V .55A 6UDFN
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	3000 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	6-UDFN Exposed Pad
Supplier Device-Gehäuse	U-DFN2020-6 (Type E)
Verlustleistung (max)	630mW (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	300V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	550mA (Ta)
Rds On (Max) @ Id, Vgs	4 Ohm @ 300mA, 10V
VGS (th) (Max) @ Id	2.8V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	7.6nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	187.3pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	2.7V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)

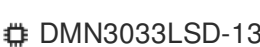
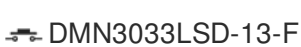
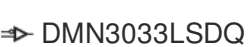
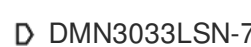
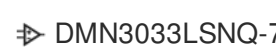

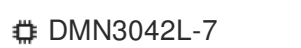
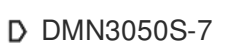
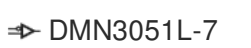
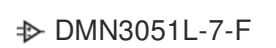
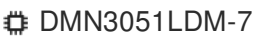
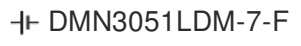
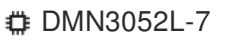
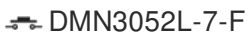
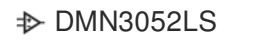
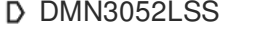
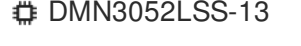
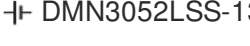
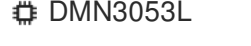
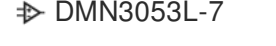
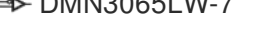
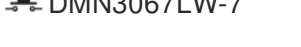
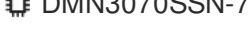
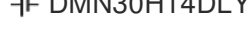
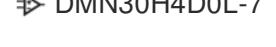
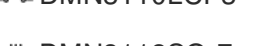
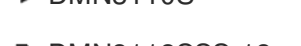
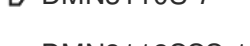
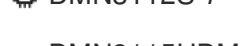
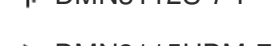


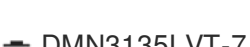
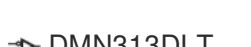
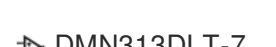
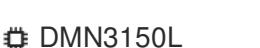
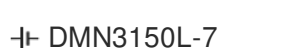
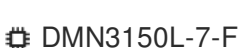
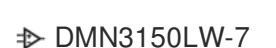


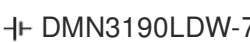







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Sie können auch interessiert sein:

 <p><b>DMN30H14DLY-13</b> Diodes Incorporated MOSFET N-CH 300V .21A SOT-89</p>	 <p><b>DMN3110S</b> D DMN3110S D</p>	 <p><b>DMN3110S-7</b> Diodes Incorporated MOSFET N-CH 30V 2.5A SOT-23</p>	 <p><b>DMN30H4D0L-13</b> Diodes Incorporated MOSFET N-CH 300V .25A SOT23</p>
 <p><b>DMN30H4D0L-7</b> Diodes Incorporated MOSFET N-CH 300V .25A SOT-23</p>	 <p><b>DMN3070SSN-7</b> Diodes Incorporated MOSFET N-CH 30V 4.2A SC59</p>	 <p><b>DMN3110LCP3</b> Diodes Incorporated DMN3110LCP3 DIODES</p>	 <p><b>DMN30H4D0LFDE-13</b> Diodes Incorporated MOSFET N-CH 300V 0.55A 6UDFN</p>

### heiße Teile

Mehr

 DMN3033LSD-13	 DMN3033LSD-13-F	 DMN3033LSDQ	 DMN3033LSN-7	 DMN3033LSNQ-7
 DMN3042L	 DMN3042L-7	 DMN3050S-7	 DMN3051L-7	 DMN3051L-7-F
 DMN3051LDM-7	 DMN3051LDM-7-F	 DMN3052L-7	 DMN3052L-7-F	 DMN3052LS
 DMN3052LSS	 DMN3052LSS-13	 DMN3052LSS-13-F	 DMN3053L	 DMN3053L-7
 DMN3065LW-7	 DMN3067LW-7	 DMN3070SSN-7	 DMN30H14DLY-13	 DMN30H4D0L-7
 DMN3110LCP3	 DMN3110S	 DMN3110S-7	 DMN3112S-7	 DMN3112S-7-F
 DMN3112SQ-7	 DMN3112SSS-13	 DMN3112SSS-13-F	 DMN3115UDM	 DMN3115UDM-7
 DMN3115UDM-7-F	 DMN3135LVT	 DMN3135LVT-7	 DMN313DLT	 DMN313DLT-7
 DMN3150L	 DMN3150L-7	 DMN3150L-7-F	 DMN3150LW	 DMN3150LW-7
 DMN3150LW-7-F	 DMN3190LDW	 DMN3190LDW-7	 DMN31D5UFZ	 DMN31D6UT

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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